



Integrated Device Technology, Inc.  
2975 Stender Way, Santa Clara, CA - 95054

## PRODUCT/PROCESS CHANGE NOTICE (PCN)

PCN #: SM-9912-01      DATE: 12/6/99  
Product Affected: 70V25 Family  
Refer to attached list of affected Part No.'s  
Manufacturing Location Affected: N/A  
Date Effective: 3/6/00

### MEANS OF DISTINGUISHING CHANGED DEVICES:

- ☒ Product Mark      Applies to "V" Die Revision only  
☐ Back Mark  
☒ Date Code      Top Mark Date Code 0010 and later  
☐ Other

Contact: Mary Vesey

Title: Product Assurance Manager

Additional Data: Attachment - Page 1-3

Phone #: (831) 754-4565

Fax #: (831) 754-4672

Samples: Available on request. Contact your local  
IDT Sales Representative

E-mail: mary.vesey@idt.com

### DESCRIPTION AND PURPOSE OF CHANGE:

- ☐ Die Technology  
☐ Wafer Fabrication Process  
☐ Assembly Process  
☐ Equipment  
☐ Material  
☐ Testing  
☐ Manufacturing Site  
☒ Data Sheet

Data Sheet changes for power and current values. Refer to attachment for details.  
This change is being made to allow for the increase in speed of the 3.3V products.

### RELIABILITY/QUALIFICATION SUMMARY:

Qualification and reliability data will be available upon request.

### CUSTOMER ACKNOWLEDGMENT OF RECEIPT:

IDT records indicate that you require written notification of this change. Please use the acknowledgement below or E-Mail to grant approval or request additional information. If IDT does not receive acknowledgement within 30 days of this notice it will be assumed that this change is acceptable.

Customer: \_\_\_\_\_

☐ *Approval for shipments prior to effective date.*

Name/Date: \_\_\_\_\_

E-Mail Address: \_\_\_\_\_

Title: \_\_\_\_\_

Phone# /Fax# : \_\_\_\_\_

CUSTOMER COMMENTS: \_\_\_\_\_

RECD. BY: \_\_\_\_\_

DATE: \_\_\_\_\_



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### ATTACHMENT

#### PCN Summary

**PCN Type:** Data Sheet

**Commodity** Memory

**Due Date** 1/10/00 (Response from Customer)

**Forecast or Execute** Execute

**Planned or Unplanned** Unplanned

**Data Sheet Change** Yes

#### Detail of Change

3.3V product was previously a component test option.  
The fab process is being converted to a true 3.3V process and will allow for increased speed in order to offer 15ns product. Power and current values will be increased. Refer to page 3 of attachment.

#### Conversion schedule (Estimated)

<b>Affected Part Numbers</b>	<b><u>Sample Availability</u></b>	<b><u>Production Shipments</u></b>
70V25V	1/15/00	3/6/00
70V24V	1/15/00	3/6/00
70V06V	1/15/00	3/6/00
70V05V	1/15/00	3/6/00



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#### Qualification Plan QSM-9908-09

Test Vehicle: 70V25V

Expected Completion Date:

1/15/00 2/15/00

	Lot SS / Acc #	Lot # 1	Lot # 2
Dynamic Life Test: 750 hours @ +135°C, 6Vcc	116 / 0		
HAST: 100 hours @ +130°C/85% R.H. 100 hours. Biased	45 / 0		
ESD: Human Body Model	12 / 0		
ESD: Charged Device Model	12 / 0		
Latch-Up Immunity	6 / 0		

**Characterization Data:** Characterization data will be completed as part of product qualification and data available upon request.



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70V25, 70V24, 70V06, 70V05

Data Sheet Changes

		25ns		35ns		55ns		Units
Icc	Commercial	Typ.	Max.	Typ.	Max.	Typ.	Max.	
	S	130	190	120	180	120	180	mA
	L	125	165	115	155	115	155	mA
		25ns		35ns		55ns		Units
Isb1	Commercial	Typ.	Max.	Typ.	Max.	Typ.	Max.	
	S	16	30	13	25	13	25	mA
	L	13	25	11	20	11	20	mA
		25ns		35ns		55ns		Units
Isb2	Commercial	Typ.	Max.	Typ.	Max.	Typ.	Max.	
	S	75	110	70	100	70	100	mA
	L	72	95	65	90	65	90	mA
		25ns		35ns		55ns		Units
Isb3	Commercial	Typ.	Max.	Typ.	Max.	Typ.	Max.	
	S	1	5	1	5	1	5	mA
	L	0.2	2.5	0.2	2.5	0.2	2.5	mA
		25ns		35ns		55ns		Units
Isb4	Commercial	Typ.	Max.	Typ.	Max.	Typ.	Max.	
	S	75	105	65	100	65	100	mA
	L	70	90	60	85	60	85	mA